

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

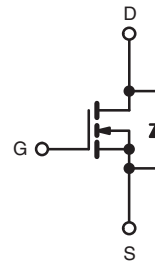
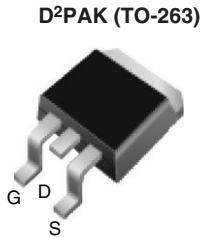
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^{a, e}	Q _g (Max)
60	0.023 at V _{GS} = 10 V	50	66 nC
	0.027 at V _{GS} = 4.5 V	40	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Logic-Level Gate Drive
- Fast Switching
- Compliant to RoHS Directive 2002/95/EC



RoHS*
 COMPLIANT
 HALOGEN
FREE
 Available



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	60	V
Gate-Source Voltage			V _{GS}	± 10	
Continuous Drain Current ^f	V _{GS} at 10 V	T _C = 25 °C	I _D	50	A
Continuous Drain Current		T _C = 100 °C		36	
Pulsed Drain Current ^a			I _{DM}	200	
Linear Derating Factor				1.0	W/°C
Linear Derating Factor (PCB Mount) ^e				0.025	
Single Pulse Avalanche Energy ^b			E _{AS}	400	mJ
Maximum Power Dissipation	T _C = 25 °C		P _D	150	W
Maximum Power Dissipation (PCB Mount) ^e	T _A = 25 °C			3.7	
Peak Diode Recovery dV/dt ^c			dV/dt	4.5	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature) ^d	for 10 s			300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- V_{DD} = 25 V, starting T_J = 25 °C, L = 179 μH, R_g = 25 Ω, I_{AS} = 51 A (see fig. 12).
- I_{SD} ≤ 51 A, di/dt ≤ 250 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 175 °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).
- Current limited by the package, (die current = 51 A).

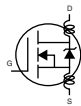
THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	40	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.0	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$, $I_D = 250\text{ }\mu\text{A}$		60	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.070	-	V/ $^\circ\text{C}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$		1.0	-	3.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 10\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 48\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 21\text{ A}^b$	-	23	-	Ω
		$V_{GS} = 4.5\text{ V}$	$I_D = 15\text{ A}^b$	-	27	-	
Forward Transconductance	g_{fs}	$V_{DS} = 25\text{ V}$, $I_D = 21\text{ A}^b$		23	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5		-	3000	-	pF
Output Capacitance	C_{oss}			-	1000	-	
Reverse Transfer Capacitance	C_{rss}			-	200	-	
Total Gate Charge	Q_g	$V_{GS} = 5.0\text{ V}$	$I_D = 51\text{ A}$, $V_{DS} = 48\text{ V}$, see fig. 6 and 13 ^b	-	60	-	nC
Gate-Source Charge	Q_{gs}			-	10	-	
Gate-Drain Charge	Q_{gd}			-	40	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}$, $I_D = 51\text{ A}$, $R_g = 4.6\text{ }\Omega$, $R_D = 0.56\text{ }\Omega$, see fig. 10 ^b		-	17	-	ns
Rise Time	t_r			-	230	-	
Turn-Off Delay Time	$t_{d(off)}$			-	42	-	
Fall Time	t_f			-	110	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	50 ^c	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	200	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = 51\text{ A}$, $V_{GS} = 0\text{ V}^b$		-	-	2.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = 51\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$		-	130	180	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	0.84	1.3	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

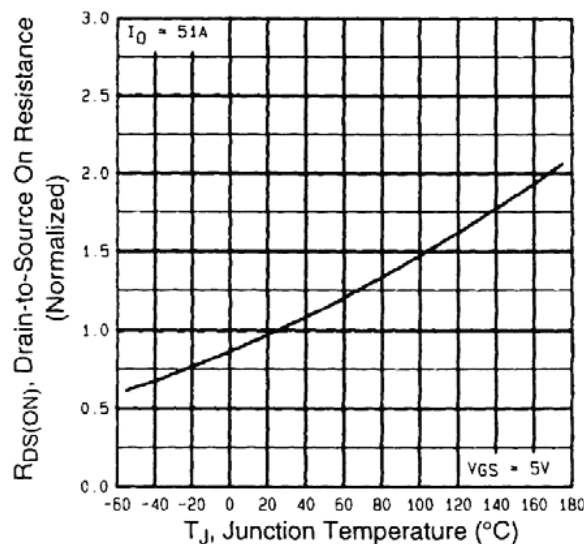
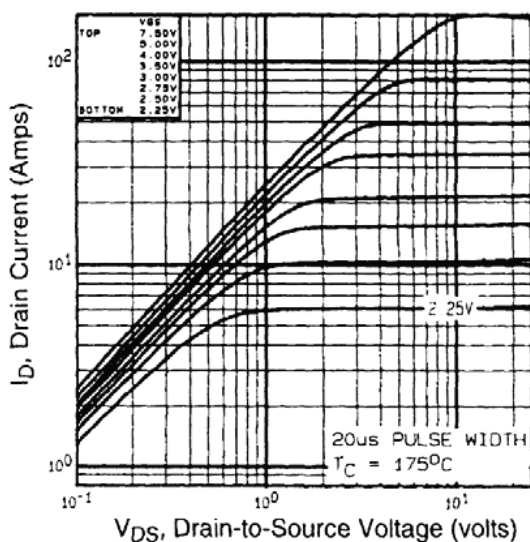
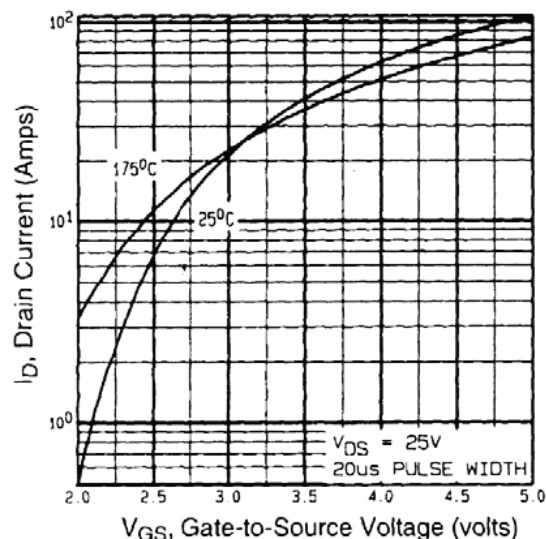
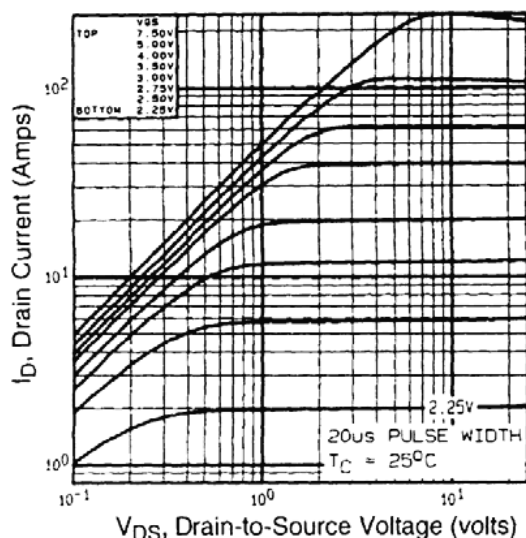
Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

c. Current limited by the package, (Die Current = 51 A).

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



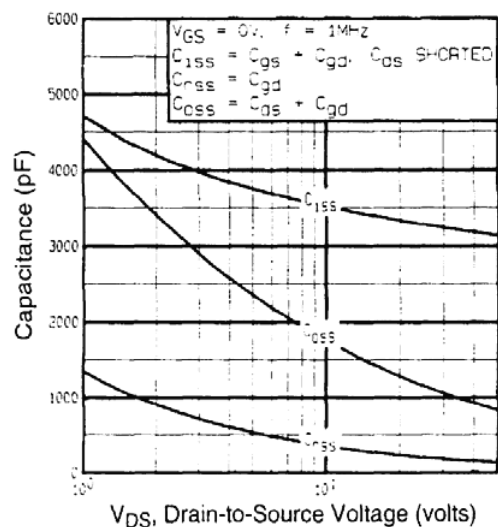


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

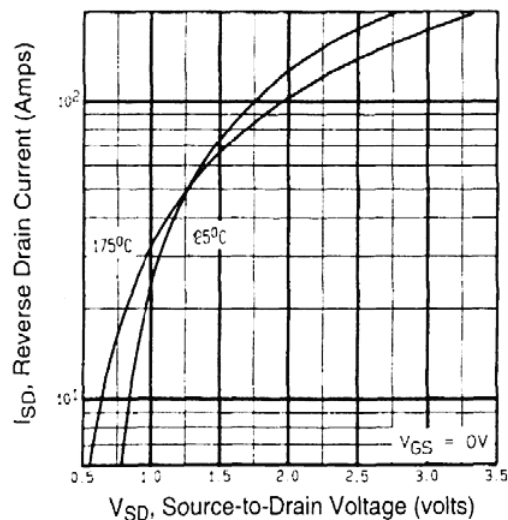


Fig. 7 - Typical Source-Drain Diode Forward Voltage

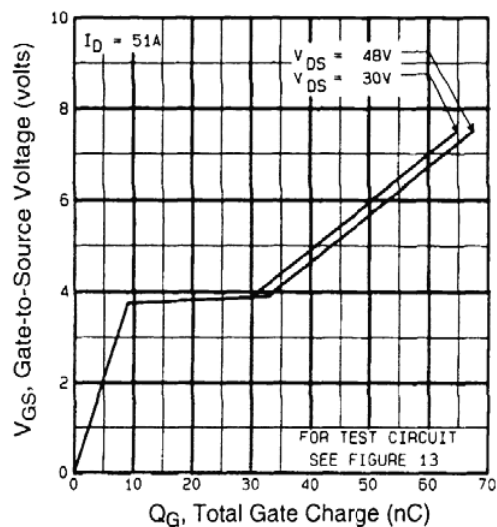


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

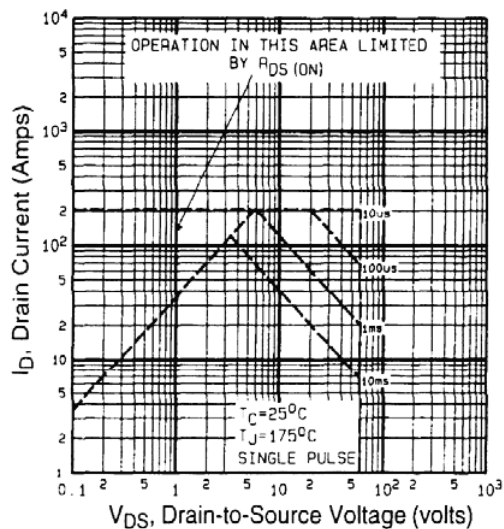


Fig. 8 - Maximum Safe Operating Area

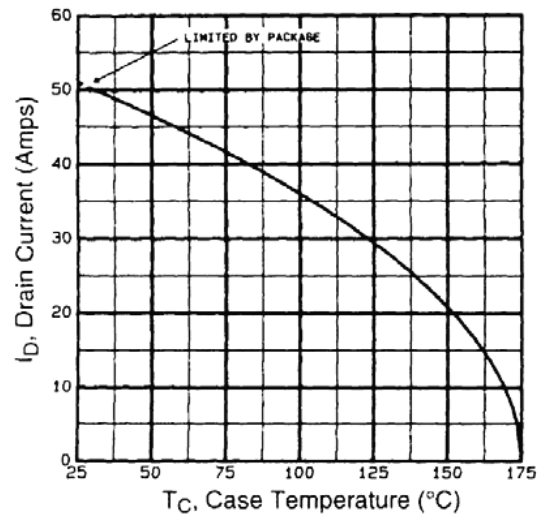


Fig. 9 - Maximum Drain Current vs. Case Temperature

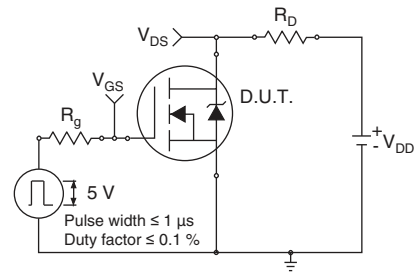


Fig. 10a - Switching Time Test Circuit

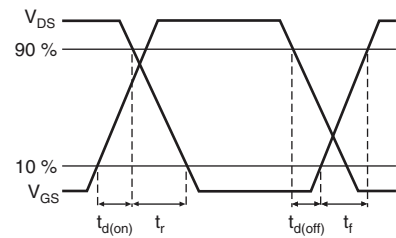


Fig. 10b - Switching Time Waveforms

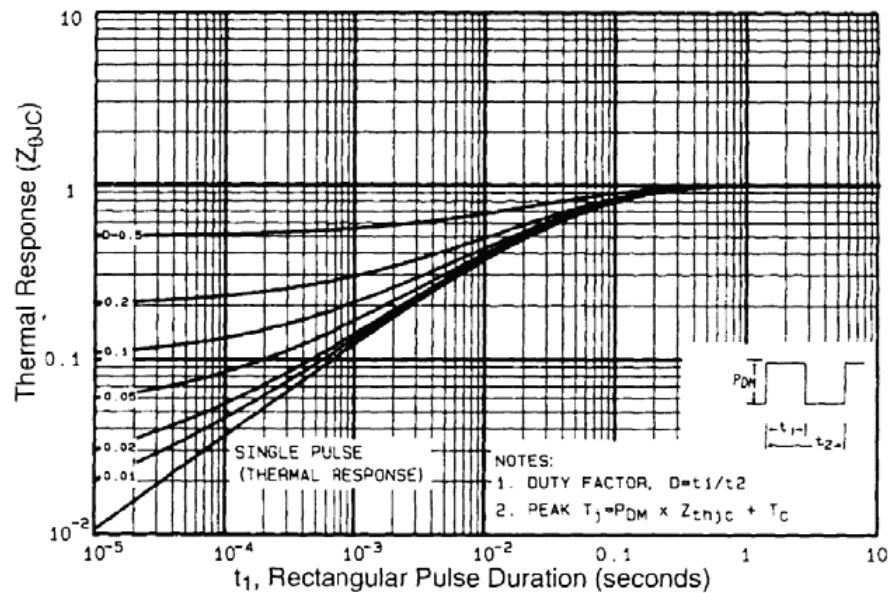


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

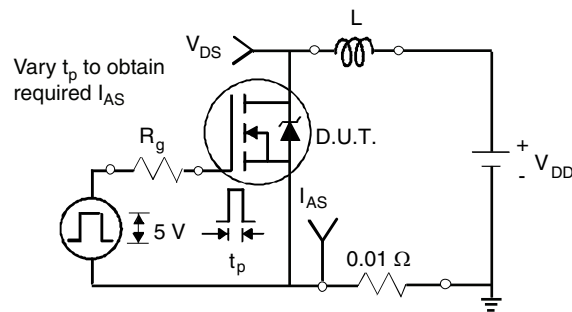


Fig. 12a - Unclamped Inductive Test Circuit

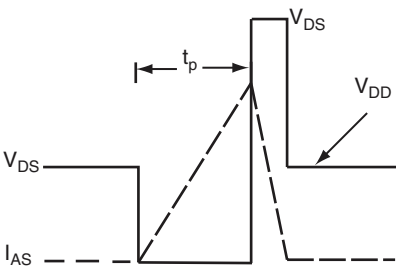


Fig. 12b - Unclamped Inductive Waveforms

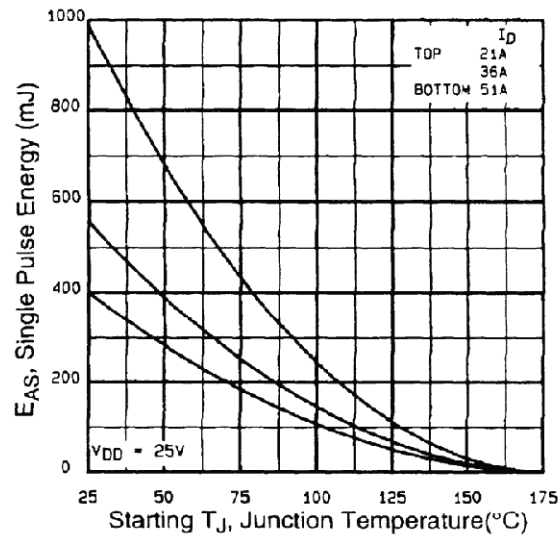


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

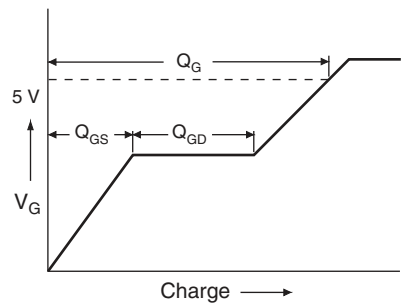


Fig. 13a - Basic Gate Charge Waveform

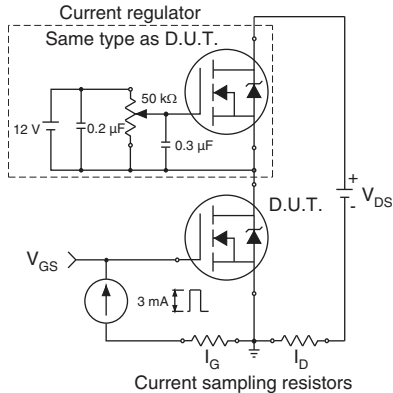


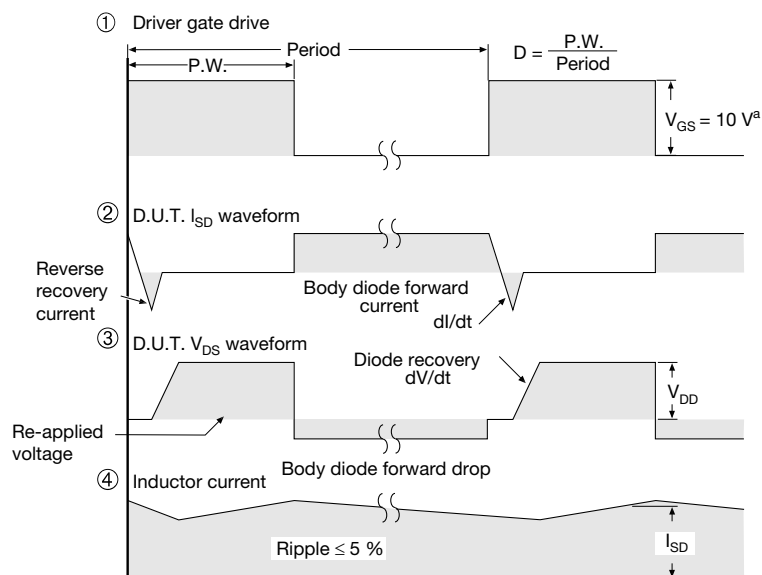
Fig. 13b - Gate Charge Test Circuit

Circuit layout considerations

- Low stray inductance
- Ground plane
- Low leakage inductance current transformer

Device parameters and components:

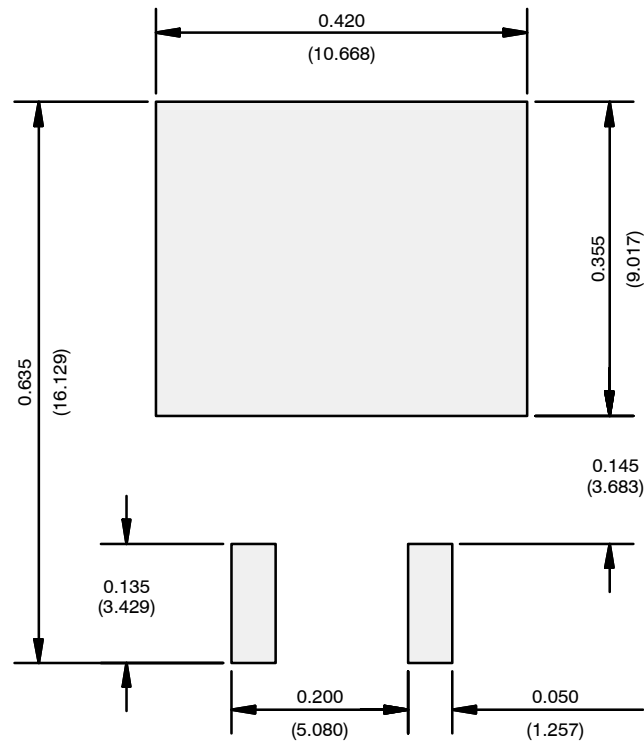
- ①: Pulse source
- ②: Driver MOSFET
- ③: Transformer
- ④: Load resistor
- R_g : Gate resistor
- V_{DD} : Supply voltage
- dV/dt controlled by R_g
- Driver same type as D.U.T.
- I_{SD} controlled by duty factor “D”
- D.U.T. - device under test



a. $V_{GS} = 5 \text{ V}$ for logic level devices

Fig. 14 - For N-Channel

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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